

## **isc** Silicon NPN Power Transistor

## 2SC5128

#### DESCRIPTION

- Collector–Emitter Breakdown Voltage
- : V<sub>(BR)CEO</sub>= 500V(Min)
- High Speed Switching
- Full-pack package with outstanding insulation, which can be in staled to the heat sink with one screw
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

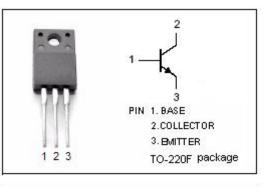
### **APPLICATIONS**

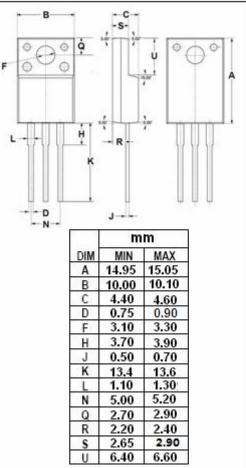
• Designed for switching regulator and general purpose applications.

SYMBOL	PARAMETER	VALUE	UNIT	
V <sub>CBO</sub>	Collector-Base Voltage	800	V	
V <sub>CEO</sub>	Collector-Emitter Voltage	500	V	
V <sub>EBO</sub>	Emitter-Base Voltage	8	V	
lc	Collector Current-Continuous	5	A	
I <sub>CM</sub>	Collector Current-peak	10	A	
I <sub>B</sub>	Base Current	3	А	
Pc	Collector Power Dissipation $T_C$ =25 °C	40	W	
Ti	Junction Temperature	150	°C	
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C	

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#### ABSOLUTE MAXIMUM RATINGS(Ta=25°C)







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## **ELECTRICAL CHARACTERISTICS**

#### $T_c = 25^{\circ}C$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	МАХ	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 25mA; I <sub>B</sub> = 0	500			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.0	V
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A			1.5	V
І <sub>сво</sub>	Collector Cutoff Current	V <sub>CB</sub> = 600V; I <sub>E</sub> = 0			0.1	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			0.1	mA
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 2A; V <sub>CE</sub> = 5V	8			
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 0.1A; V <sub>CE</sub> = 5V	15			
fT	Current-Gain—Bandwidth Product	I <sub>E</sub> = -0.5 A; V <sub>CE</sub> = 10V		20		MHz

Switching Times

ton	Turn-On Time	I <sub>C</sub> = 2A; V <sub>CC</sub> = 200V; R <sub>L</sub> = 100 Ω I <sub>B1</sub> = 0.4A; I <sub>B2</sub> = -0.8A;		1.0	μ \$
ts	Storage Time			3	μ \$
t <sub>f</sub>	Fall Time			0.3	μ <b>S</b>

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